

SPN6335

DESCRIPTION

The SPN6335 is the Dual N-Channel enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology. This high density process is especially tailored to minimize on-state resistance and provide superior switching performance. These devices are particularly suited for low voltage applications such as notebook computer power management and other battery powered circuits where high-side switching , low in-line power loss, and resistance to transients are needed.

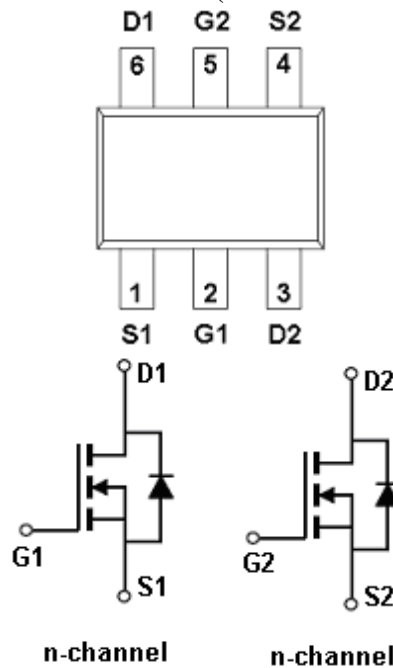
FEATURES

- ◆ N-Channel
20V/0.95A, $R_{DS(ON)}=380m\Omega@V_{GS}=4.5V$
20V/0.75A, $R_{DS(ON)}=450m\Omega@V_{GS}=2.5V$
20V/0.65A, $R_{DS(ON)}=800m\Omega@V_{GS}=1.8V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOT-363 (SC-70-6L) package design

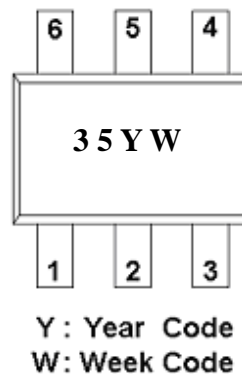
APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOT-363 / SC-70-6L)



PART MARKING



SPN6335

PIN DESCRIPTION

Pin	Symbol	Description
1	S1	Source 1
2	G1	Gate 1
3	D2	Drain 2
4	S2	Source 2
5	G2	Gate 2
6	D1	Drain1

ORDERING INFORMATION

Part Number	Package	Part Marking
SPN6335S36RG	SOT-363	35YW
SPN6335S36RGB	SOT-363	35YW

※ Week Code : A ~ Z(1 ~ 26) ; a ~ z(27 ~ 52)

※ SPN6335S36RG : Tape Reel ; Pb – Free

※ SPN6335S36RGB : Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	TA=25°C	1.2
		TA=80°C	0.9
Pulsed Drain Current	I _{DM}	4	A
Continuous Source Current(Diode Conduction)	I _S	0.6	A
Power Dissipation	P _D	TA=25°C	0.35
		TA=70°C	0.19
Operating Junction Temperature	T _J	-55/150	°C
Storage Temperature Range	T _{STG}	-55/150	°C

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ELECTRICAL CHARACTERISTICS

(TA=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.35		1.0	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$			1	uA
		$V_{DS}=20V, V_{GS}=0V$ $T_J=55^\circ C$			5	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 4.5V, V_{GS}=5V$	0.7			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=0.95A$		0.26	0.38	Ω
		$V_{GS}=2.5V, I_D=0.75A$		0.32	0.45	
		$V_{GS}=1.8V, I_D=0.65A$		0.42	0.80	
Forward Transconductance	g_{fs}	$V_{DS}=10V, I_D=0.4A$		1.0		S
Diode Forward Voltage	V_{SD}	$I_S=0.15A, V_{GS}=0V$		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=10V, V_{GS}=4.5V,$ $I_D=0.6A$		1.2	1.5	nC
Gate-Source Charge	Q_{gs}			0.2		
Gate-Drain Charge	Q_{gd}			0.3		
Turn-On Time	$t_{d(on)}$	$V_{DD}=10V, R_L=10\Omega,$ $I_D=0.5A$ $V_{GEN}=4.5V, R_G=6\Omega$		5	10	ns
	t_r			8	15	
Turn-Off Time	$t_{d(off)}$			10	18	
	t_f			1.2	2.8	